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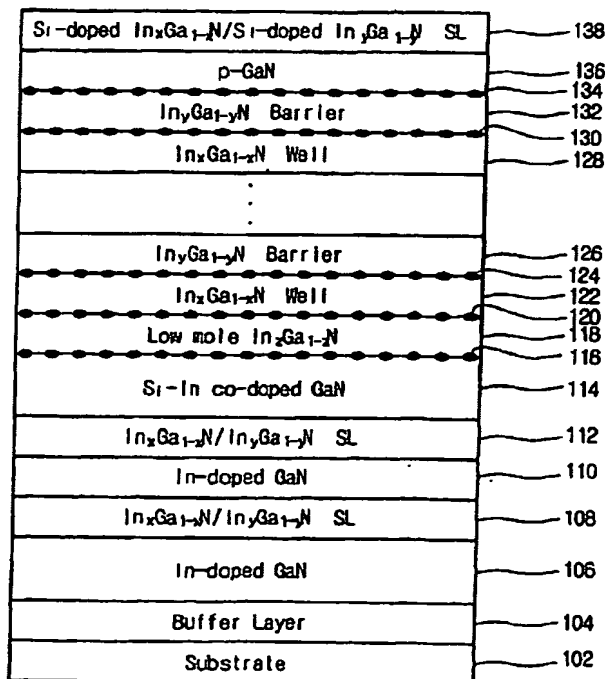
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(54) Title: NITRIDE SEMICONDUCTOR LIGHT EMITTING DEVICE



(57) Abstract: A nitride semiconductor light emitting device is provided. The nitride semiconductor light emitting device includes: an n-type nitride semiconductor layer; an In-containing super lattice structure layer formed above the n-type nitride semiconductor layer; a first electrode contact layer formed above the super lattice structure layer; a first cluster layer formed above the first electrode contact layer; a first In-containing nitride gallium layer formed above the first cluster layer; a second cluster layer formed above the first In-containing nitride gallium layer; an active layer formed above the second cluster layer, for emitting light; a p-type nitride semiconductor layer formed above the active layer; and a second electrode contact layer formed above the p-type nitride semiconductor layer.

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